

AMENDMENTS TO THE CLAIMS

1. (cancelled)
2. (cancelled)
3. (cancelled)
4. (cancelled)
5. (cancelled)

6. (currently amended) An interlevel dielectric structure comprising:

a single first dielectric layer situated on a semiconductor substrate, said single first dielectric layer having an upper surface;

a plurality of lines ~~comprised~~ of a two-layer conductive material extending along said upper surface of said single first dielectric layer; wherein:

each line of said plurality of lines has an upper surface, a lower surface, and at least one side surface;

adjacent lines of said plurality of lines have spaces situated therebetween;

a first layer of the two-layer conductive material ~~the lower surfaces of each~~
~~line~~ of said plurality of lines is in contact with said upper surface of said single first dielectric layer; and

a second layer of the two-layer conductive material ~~the upper surface of~~ at

least one side surface;

a single second dielectric layer above both said plurality of lines and said single first

dielectric layer, said single second dielectric layer having a lower surface in contact with the upper surface of each line of said plurality of lines; and

a single dielectric material situated in said space between adjacent lines of said plurality of lines, said single dielectric material not extending over the upper surface of each line of said plurality of lines, ~~the~~ an upper surface of said single dielectric material being higher than the upper surface of each line of said plurality of lines, ~~the~~ and a lower surface of said single dielectric material being lower than the lower surface of each line of said plurality of lines.

7. (currently amended) The interlevel dielectric structure as defined in Claim 6, wherein:

said layer of refractory metal nitride has an electrical insulation spacer layer thereon, said electrical insulation spacer layer having thereon said single second dielectric layer; and

at least one side surface of the single dielectric material is in contact with at least one side surface of at least one of the plurality of lines.

8. (previously presented) The interlevel dielectric structure as defined in Claim 7, wherein said electrical insulation spacer layer is a silicon dioxide layer.

9. (original) The interlevel dielectric structure as defined in Claim 6, wherein said refractory

10. (previously presented) The interlevel dielectric structure as defined in Claim 6, wherein

11. (previously presented) The interlevel dielectric structure as defined in Claim 6, wherein at least one of the single first dielectric layer and single second dielectric layer comprises silicon dioxide.

12. (currently amended) The interlevel dielectric structure as defined in Claim 6, wherein said conductive material of the first layer is selected from the group consisting of polysilicon, aluminum, copper, tungsten, ~~or any~~ and combinations thereof.

13. (currently amended) The interlevel dielectric structure as defined in Claim 6, ~~where~~ wherein the single dielectric material has a dielectric constant of less than about 3.6.

14. (currently amended) An interlevel dielectric structure comprising:

a first dielectric layer situated on a semiconductor substrate, said first dielectric layer having an upper surface;

a plurality of lines ~~comprised~~ of a two layer conductive material extending along said upper surface of said first dielectric layer; wherein:

each line of said plurality of lines has an upper surface, a lower surface, and at least one side surface;

line of said plurality of lines is in contact with said upper surface of said first

a second layer of the two-layer conductive material ~~the upper surface of at least one line~~ of said plurality of lines ~~has thereon~~ comprises a layer of titanium nitride;

said layer of titanium nitride has thereon a silicon dioxide spacer layer; and

said silicon dioxide spacer layer not being in contact with at least one side surface of at least one of the plurality of lines;

a second dielectric layer above both said plurality of lines and said first dielectric layer, said second dielectric layer having a lower surface in contact with the silicon dioxide spacer layer of each line of said plurality of lines; and

a dielectric material, having at least one side surface, situated in said space between adjacent lines of said plurality of lines, said dielectric material not extending over the upper surface of each line of said plurality of lines, ~~the~~ an upper surface of said dielectric material being higher than the upper surface of each line of said plurality of lines, ~~the~~ a lower surface of said dielectric material being lower than the lower surface of each line of said plurality of lines, and at least one side surface of the dielectric material being in contact with at least one side surface of at least one of the plurality of lines.

15. (original) The interlevel dielectric structure as defined in Claim 14, wherein said dielectric material comprises PTFE.

of the first and second dielectric layers comprises silicon dioxide.

17. (currently amended) The interlevel dielectric structure as defined in Claim 14, wherein said conductive material of the first layer is selected from the group consisting of polysilicon, aluminum, copper, tungsten, ~~or any~~ and combinations thereof.

18. (currently amended) The interlevel dielectric structure as defined in Claim 14, ~~where~~ wherein the dielectric material has a dielectric constant of less than about 3.6.